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Advances in Patterning Materials and Processes XXXII

**Thomas I. Wallow
Christoph K. Hohle**
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Douglas Guerrero, Brewer Science, Inc. (United States)
- 7 Materials and Etch in Emerging Technologies: Joint Session with Conferences 9425 and 9428
Christoph K. Hohle, Fraunhofer Institute for Photonic Microsystems (Germany)
Qinghuang Lin, IBM Thomas J. Watson Research Center (United States)
- 8 DSA Materials and Processes I: Joint Session with Conferences 9425 and 9423
Juan J. de Pablo, The University of Chicago (United States)
Roel Gronheid, IMEC (Belgium)

- 9 DSA Materials and Processes II: Joint Session with Conferences 9425 and 9423
Todd R. Yountin, Intel Corporation (United States)
Sean D. Burns, IBM Corporation (United States)
- 10 EUV Resists and Processes
Katsumi Ohmori, Tokyo Ohka Kogyo Company, Ltd. (Japan)
Ramakrishnan Ayothi, JSR Micro, Inc. (United States)
- 11 DSA Materials and New Concepts
Mark H. Somervell, Tokyo Electron America, Inc. (United States)
Daniel P. Sanders, IBM Research - Almaden (United States)
- 12 New Patterning Processes
Ralph R. Dammel, EMD Performance Materials Corporation (United States)
Scott W. Jessen, Texas Instruments Inc. (United States)
- 13 Materials and Process Engineering
Thomas I. Wallow, ASML Brion Technologies (United States)
Clifford L. Henderson, Georgia Institute of Technology (United States)